Correction

APPLIED PHYSICAL SCIENCES

Correction for "Large enhancement of thermoelectric performance in MoS_2/*h*-BN heterostructure due to vacancy-induced band hybridization," by Jing Wu, Yanpeng Liu, Yi Liu, Yongqing Cai, Yunshan Zhao, Hong Kuan Ng, Kenji Watanabe, Takashi Taniguchi, Gang Zhang, Cheng-Wei Qiu, Dongzhi Chi, A. H. Castro Neto, John T. L. Thong, Kian Ping Loh, and Kedar Hippalgaonkar, which was first published June 10, 2020; 10.1073/pnas.2007495117 (*Proc. Natl. Acad. Sci. U.S.A.* **117**, 13929–13936).

The authors note that one of the three affiliations listed for Kian Ping Loh was incorrect. This author does not have an affiliation with Institute of High Performance Computing, Agency for Science, Technology and Research, 138632, Singapore. Instead, this author should have been shown as having a third affiliation at Shenzhen University-National University of Singapore Collaborative Innovation Center for Optoelectronic Science and Technology, Shenzhen University, Shenzhen, 518060, China. The corrected author and affiliation lines appear below. The online version has been corrected.

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